

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Specification

The paragraph at page 10, lines 5-14 has been amended as follows:

FIGS. 1A and 1B are top and bottom perspective views, respectively, of semiconductor chip 110 which is an integrated circuit in which various transistors, circuits, interconnect lines and the like are formed (not shown). Chip 110 includes opposing major surfaces 112 and 114 and has a thickness of 200 microns between these surfaces. Surface 112 is an upper surface, and surface 114 is a lower surface. Surface 112 is the active surface and includes conductive pads 116 arranged in a single row and passivation layer 118. Pads 116 are substantially aligned with passivation layer 118 so that surface 112 is essentially flat. Alternatively, if desired, pads 116 can extend above or be recessed below passivation layer 118. Pads 116 provides bonding sites to electrically couple chip 110 with external circuitry. Thus, a particular pad 116 can be input/output pad or a power/ground pad. Pads 116 have a length and width of 70 microns.

The paragraph at page 16, lines 10-13 has been amended as follows:

FIG. 5C is an enlarged plan view of encircled detail 5C in FIG. 5A that shows a representative pad 116 and routing line 148 in greater detail. Since pad 116 and routing line 148 are not be-visible from surface 114 of chip 110, they are shown in phantom. Routing line 148 includes a distal end that overlaps pad 116.

The paragraph at page 19, lines 27-31 has been amended as follows:

A suitable wet chemical etch can be provided by the same solution used to form slots 128 and recessed portions 130, 132 and 134. The optimal etch time for exposing the structure to the wet chemical etch without excessively exposing the portions of leads 138 embedded in peripheral portion 166 and adjacent to inner side surfaces 174 **after** the selected copper has been removed can be established through trial and error.

The paragraph at page 23, line 23 to page 24, line 6 has been amended as follows:

At this stage, device 186 includes chip 110, conductive traces 150, adhesive 154, connection joints 180 and insulative housing 184. Conductive traces 150 each include a lead 138 that protrudes laterally from and extends through a side surface 162 of insulative housing 184, a terminal 146 that protrudes downwardly from and extends through bottom surface 164 of insulative housing 184, and a routing line 148 within insulative housing 184 that is integral with an associated terminal 146 and contacts an associated lead 138 and connection joint 180. Conductive traces 150 are electrically connected to pads 116 by connection joints 180 in one-to-one relation, and are electrically isolated from one another. Leads 138 are arranged in opposing rows that protrude laterally from and extend through opposing side surfaces 162 and are disposed between top surface 160 and bottom surface 164. Terminals 146 are arranged as an array that protrudes downwardly from and extends through bottom surface 164 and is disposed inside inner side surfaces 174. Furthermore, leads 138 and terminals 146 are spaced and separated from one another outside insulative housing 184, and leads 138 and terminals 146 are electrically connected to one another and to pads 116 inside insulative housing 184 and outside chip 110.

The paragraph at page 25, lines 16-24 has been amended as follows:

Advantageously, the present invention provides a semiconductor package device that has ~~have~~ a first electrode configuration for the test socket and a second electrode configuration for the next level assembly. The first electrode configuration is provided by the leads, and the second electrode configuration is provided by the terminals. As a result, the device is flexible enough to accommodate test sockets and printed circuit boards with different electrical contact requirements. In other words, the leads can be optimized for mating with the test socket, and the terminals can be optimized for mating with the next level assembly. In this manner, the device can be tested using a standard test socket, and then attached to a printed circuit board with an entirely different contact arrangement than the test socket.

The paragraph at page 30, line 22 to page 31, line 9 has been amended as follows:

The connection joints can be formed from a wide variety of materials including copper, gold, nickel, palladium, tin, alloys thereof, and combinations thereof, can be formed by a wide variety of processes including electroplating, electroless plating, ball bonding, solder reflowing and conductive adhesive curing, and can have a wide variety of shapes ~~andas~~ sizes. The shape and composition of the connection joints depends on the composition of the conductive traces as well as design and reliability considerations. Further details regarding an electroplated connection joint are disclosed in U.S. Application Serial No. 09/865,367 filed May 24, 2001 by Charles W.C. Lin entitled "Semiconductor Chip Assembly with Simultaneously Electroplated Contact Terminal and Connection Joint" which is incorporated by reference. Further details regarding an electrolessly plated connection joint are disclosed in U.S. Application Serial No. 09/864,555 filed May 24, 2001 by Charles W.C. Lin entitled "Semiconductor Chip Assembly with Simultaneously Electrolessly Plated Contact Terminal and Connection Joint" which is incorporated by reference. Further details regarding a ball bond connection joint are disclosed in U.S. Application Serial No. 09/864,773 filed May 24, 2001 by Charles W.C. Lin entitled "Semiconductor Chip Assembly with Ball Bond Connection Joint" which is incorporated by reference. Further details regarding a solder or conductive adhesive connection joint are disclosed in U.S. Application Serial No. 09/927,216 filed August 10, 2001 by Charles W.C. Lin entitled "Semiconductor Chip Assembly with Hardened Connection Joint" which is incorporated by reference.

The paragraph at page 32, lines 18-22 has been amended as follows:

For instance, if an optoelectronic chip is employed with a light sensitive cell and pads on the upper surface, the pads, adhesive, conductive traces and connection joints are disposed outside the light sensitive cell, and the insulative base is a transparent epoxy layer that is deposited on the light sensitive cell, then the light sensitive cell will ~~receive~~~~be exposed to~~ light from the external environment that impinges upon and passes through the insulative base.

In the Claims

The claims have been amended as follows:

1 11. (Amended) A semiconductor package device, comprising:
2 an insulative housing with a top surface, a bottom surface, and a peripheral side surface
3 between the top and bottom surfaces;
4 a semiconductor chip within and surrounded by the insulative housing, wherein the chip
5 includes an upper surface and a lower surface, the upper surface includes a conductive pad, the
6 upper surfaces faces towards the bottom surface and faces away from the top surface, and the
7 insulative housing contacts the lower surface;
8 a terminal that protrudes downwardly from and extends through the bottom surface and is
9 spaced from the side surface and is electrically connected to the pad; and
10 a lead that protrudes laterally from and extends through the side surface and is electrically
11 connected to the pad, wherein the terminal and the lead are spaced and separated from one
12 another outside the insulative housing, and the terminal and the lead are electrically connected to
13 one another inside the insulative housing and outside the chip.

1 31. (Amended) A semiconductor package device, comprising:
2 an insulative housing with a top surface, a bottom surface, and four peripheral side
3 surfaces between the top and bottom surfaces, wherein the bottom surface includes a peripheral
4 portion shaped as a rectangular peripheral ledge adjacent to the side surfaces and a recessed
5 central portion within the peripheral portion and spaced from the side surfaces, and the peripheral
6 portion protrudes downwardly from the central portion and extends a first distance below the
7 central portion;
8 a semiconductor chip within and surrounded by the insulative housing, wherein the chip
9 includes an upper surface and a lower surface, the upper surface includes a conductive pad, the
10 upper surfaces faces towards the bottom surface and faces away from the top surface, and the
11 insulative housing contacts the lower surface;

12 a terminal that protrudes downwardly from and extends through the central portion of the
13 bottom surface and is spaced from the side surfaces and is electrically connected to the pad,
14 wherein the terminal extends a second distance below the central portion, and the first distance is
15 greater than the second distance; and

16 a lead that protrudes laterally from and extends through one of the side surfaces and is
17 electrically connected to the pad, wherein the terminal and the lead are spaced and separated
18 from one another outside the insulative housing, and the terminal and the lead are electrically
19 connected to one another inside the insulative housing and outside the chip.

1 41. (Amended) A semiconductor package device, comprising:

2 an insulative housing with a top surface, a bottom surface, and a peripheral side surface
3 between the top and bottom surfaces;

4 a semiconductor chip within the insulative housing, wherein the chip includes an upper
5 surface and a lower surface, and the upper surface includes a conductive pad;

6 a terminal that protrudes downwardly from and extends through the bottom surface and is
7 electrically connected to the pad; and

8 a lead that protrudes laterally from and extends through the side surface and is electrically
9 connected to the pad, wherein the lead includes a recessed portion that extends **into the**
10 **insulative housing** ~~through the side surface~~ and is spaced from the top and bottom surfaces and a
11 non-recessed portion that extends outside the insulative housing and is adjacent to the recessed
12 portion and ~~a corner between the side surface and the bottom surface~~, the terminal and the lead
13 are spaced and separated from one another outside the insulative housing, and the terminal and
14 the lead are electrically connected to one another inside the insulative housing and outside the
15 chip.

1 51. (Amended) A semiconductor package device, comprising:

2 an insulative housing with a top surface, a bottom surface, and a peripheral side surface
3 between the top and bottom surfaces;

4 a semiconductor chip within and surrounded by the insulative housing, wherein the chip
5 includes an upper surface and a lower surface, the upper surface includes a conductive pad, the

6 upper surfaces faces towards the bottom surface and faces away from the top surface, and the
7 insulative housing contacts the lower surface;

8 a terminal that protrudes downwardly from and extends through the bottom surface and is
9 spaced from the side surface and is electrically connected to the pad; and

10 a lead that protrudes laterally from and extends through the side surface and is electrically
11 connected to the pad, wherein the lead includes a recessed portion ~~inside the insulative housing~~
12 that extends **into the insulative housing** ~~through the side surface~~ and is spaced from the top and
13 bottom surfaces and a non-recessed portion **that extends** outside the insulative housing **and that**
14 is adjacent to ~~and integral with~~ the recessed portion and ~~contacts the side surface and is adjacent~~
15 ~~to a corner between the side surface and the bottom surface~~, the terminal and the lead are spaced
16 and separated from one another outside the insulative housing, and the terminal and the lead are
17 electrically connected to one another inside the insulative housing and outside the chip.

Claims 61-120 have been added.

REMARKS

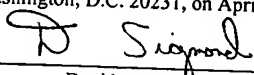
Claims 1-120 are pending. In this Preliminary Amendment, claims 11, 31, 41 and 51 have been amended, and claims 61-120 have been added. In addition, the Specification has been amended to improve clarity. No new matter has been added.

The fee for additional claims 61-120 is calculated below:

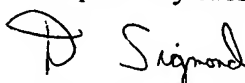
For	Claims Remaining After Amendment	Highest Number Previously Paid For		Extra Claims	Rate		Additional Fee
Total Claims	120	- 60	=	60	x \$9	=	\$540
Independent Claims	12	- 6	=	6	x \$42	=	\$252
Multiple Dep. Claim	0	0					0
Total Fee						=	\$792

Please charge the \$792 fee to Deposit Account No. 502178/BDG005 and charge any underpayment or credit any overpayment to this Account.

The application is believed to be in condition for allowance. Should any issues remain, the Examiner is encouraged to telephone the undersigned attorney.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on April 25, 2003.	
 David M. Sigmond Attorney for Applicant	<u>4, 25, 03</u> Date of Signature

Respectfully submitted,


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